

Tuesday, September 9												
10:00- Plenary (Main Convention Hall)												
Lunch												
2F Convention Hall 200	2F 201A	2F 201B	2F 202A	4F 405	4F 406	4F 403	4F 404	1F 101	2F 202B	3F 304	4F 401	4F 402
13:30-15:00 A-1:ReRAM(I)	13:30-15:00 B-1:Group-IV Optical Devices		13:30-15:15 D-1:Nano Devices for Chemical & Biosensing	13:30-15:15 E-1:GaN Devices & Characterization	13:30-15:00 F-1:Advanced Process and Reliability	13:30-15:15 G-1:3D/TSV	13:30-15:15 Area8,9&13 H-1:2D Materials (1)	13:30-15:20 J-1:Tunnel FET	13:30-15:15 K-1:Flexible Electronics and Thin-film Devices	13:30-15:15 M-1:Spin Dynamics	13:30-14:45 N-1:Processing and Growth	
Coffee Break												
15:40-17:15 A-2:ReRAM(II)	15:40-17:10 B-2:Si Photonics		15:40-17:10 D-2:Microfluidics	15:40-17:10 E-2:High-Frequency Devices & Circuits	15:40-17:25 F-2:Gate Stack Characterization	15:40-17:20 G-2:Reliability	15:40-17:25 Area8,9&13 H-2:2D Materials (2)	15:40-17:25 J-2:Characterization	15:40-16:55 Area10&15 K-2:Organic Photovoltaics I	15:40-17:25 M-2:Spin Transport	15:40-17:25 N-2:Power Devices and Modules	
18:30 - 20:30 Banquet (OKURA FRONTIER HOTEL TSUKUBA ANNEX Subaru)												
Wednesday, September 10												
2F Convention Hall 200	2F 201A	2F 201B	2F 202A	4F 405	4F 406	4F 403	4F 404	1F 101	2F 202B	3F 304	4F 401	4F 402
9:30-11:00 A-3:CBRAM/DRAM	9:30-11:15 B-3:Light Sources and Functional Devices	9:30-10:45 C-3:Growth and Process of Nitrides	9:30-10:45 D-3:Biosensors	9:30-11:15 Area6&14 E-3:GaN Power Devices	9:30-11:00 F-3:Interface and Material Science		9:30-11:15 H-3:Topological Insulators and Imaging	9:30-11:15 J-3:CMOS Platform & SRAM	9:30-11:00 Area 10 & 15 K-3:Organic Photovoltaics II	9:30-11:15 M-3:RF and Analog Techniques		9:30-11:15 P-3:Nanowire Electronics
Coffee Break												
11:30-12:30 Short Presentation Area4	11:30-12:30 Short Presentation Area7	11:30-12:30 Short Presentation Area8	11:30-12:30 Short Presentation Area11	11:30-12:30 Short Presentation Area6	11:30-12:30 Short Presentation Area1	11:30-12:30 Short Presentation Area15	11:30-12:30 Short Presentation Area9	11:30-12:30 Short Presentation Area3	11:30-12:30 Short Presentation Area10	11:30-12:30 Short Presentation Area12	11:30-12:30 Short Presentation Area14	11:30-12:30 Short Presentation Area13
										Short Presentation Area5		Short Presentation Area2
Lunch												
14:00-16:00 Poster Session (102, Multi-Purpose Hall)												
Coffee Break												
2F Convention Hall 200	2F 201A	2F 201B	2F 202A	4F 405	4F 406	4F 403	4F 404	1F 101	2F 202B	3F 304	4F 401	4F 402
16:30-17:30 A-4:FeRAM/PCRAM	16:30-17:45 Area7&12 B-4:Magneto-Optic Devices	16:30-17:30 C-4:Metal Induced Crystallization	16:30-17:45 Area5&11 D-4:Neural Interface	16:30-17:45 Area6&14 E-4:Silicon Carbide Devices	16:30-17:40 F-4:Metal Contacts and Junction Technologies	16:30-17:45 G-4:III-V and Quantum Photovoltaics	16:30-17:30 H-4:Novel Devices	16:30-17:30 J-4:Device Physics	16:30-17:45 K-4:Organic Biosensors			16:30-17:45 Area2&13 P-4:Novel Interconnects
18:30-20:00 Rump Sessions (201, 202)												
Thursday, September 11												
2F Convention Hall 200	2F 201A	2F 201B	2F 202A	4F 405	4F 406	4F 403	4F 404	1F 101	2F 202B	3F 304	4F 401	4F 402
9:30-11:00 Area4,5&12 A-6:Non Volatile Memory and Logic I	9:30-10:45 Area 2 & 7 B-6:Optical Interconnection I	9:30-10:45 C-6:Growth and Process of Oxides	9:30-10:30 D-6:Bio Molecular Analysis		10:00-10:50 Area1&14 F-6:Thermal Oxidation and MOS Interface	9:30-10:30 G-6:Compound Semiconductor Photovoltaics	9:30-10:45 Area9&12 H-6:Quantum Transport (1)	9:30-10:40 J-6:Ge & SiGe CMOS	9:30-10:45 K-6:OLED	9:30-10:50 M-6:MEMS and Energy Harvesters		9:30-10:45 P-6:Nanowire Photonics
Coffee Break												
11:15-12:15 Area4,5&12 A-7:Non Volatile Memory and Logic II	11:15-12:15 Area2&7 B-7:Optical Interconnection II	11:15-12:15 C-7:Properties of Oxides	11:15-12:30 D-7:Microdevices for Biomedical Applications	11:15-12:30 E-7:Oxide Devices	11:15-12:35 F-7:Ge Channel Devices	11:15-12:30 G-7:New Concepts	11:15-12:15 H-7:Quantum Transport (2)	11:15-12:15 J-7:Noise	11:15-12:30 K-7:Characterization			11:15-12:15 P-7:Nanocarbon Based FETs & ICs
Lunch												
14:00-15:10 A-8:MTJ/MRAM		14:00-15:15 C-8:Growth of Germanium Based Semiconductors		14:00-15:15 E-8:III-V MOS Technologies		14:00-15:15 G-8:Silicon Photovoltaics			14:00-15:00 K-8:OTFT	14:00-15:10 M-8:Wireless Circuits	14:00-15:15 N-8:Device Modeling and Characterization	14:00-15:00 P-8:Nanocarbon Growth & Applications
15:30-16:40 A-9:Flash Memory		15:30-16:15 C-9:Growth Processing of Group IV Semiconductors								15:30-16:45 M-9:Image Sensors		15:30-16:30 P-9:2D Materials & Devices

Area Scope

	Area 1: Advanced LSI Processing & Materials Science
	Area 2: Advanced Interconnect and 3D Integration/ Materials and Characterization
	Area 3: CMOS Devices / Device Physics
	Area 4: Advanced Memory Technology
	Area 5: Advanced Circuits and Systems
	Area 6: Compound Semiconductor Electron Devices & Related Technologies
	Area 7: Photonic Devices and Related Technologies
	Area 8: Advanced Material Synthesis and Crystal Growth Technology

	Area 9: Physics and Applications of Novel Functional Devices and Materials
	Area 10: Organic Materials Science, Device Physics, and Applications
	Area 11: Sensors and Materials for Biology, Chemistry and Medicine
	Area 12: Spintronics Materials and Devices
	Area 13: Applications of Nanotubes, Nanowires, and Graphene
	Area 14: Power Devices and Materials
	Area 15: Photovoltaic Materials and Devices